

The read-out ASIC for silicon drift detectors

Saturday, 10 October 2015 09:30 (30)

The paper describes the read-out ASIC for silicon X-ray drift detectors. The ASIC has been designed in CMOS 0.35 μm technology and contained two read-out channels. Each channel include preamplifier and shaper. Preamplifiers optimized for operation with detectors, having capacitances of 100 fF. The 6-th order shaper have a controllable time constants (0.5 – 8 μs).

Presentation type

Poster

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Session Classification : Poster session V

Track Classification : Methods of experimental physics